

Abstract of the Disclosure:

A method for fabricating a semiconductor structure includes providing a semiconductor substrate and a sacrificial layer between a layer to be patterned and a resist layer, patterning
5 the resist layer to form a patterned resist layer; selectively etching the sacrificial layer with a taper angle so as to reduce the dimensions within the sacrificial layer in the etching direction which are prescribed by depressions situated in the patterned resist layer, and selectively etching the
10 layer to be patterned using the sacrificial layer etched with a taper angle as a mask. The present invention also relates to a method for fabricating a semiconductor structure in which two sacrificial layers are used.

GLM/nt